

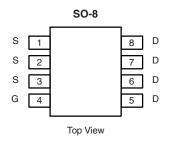
## VBA1606 Datasheet N-Channel 60 V (D-S) 175 °C MOSFET

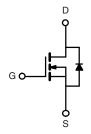
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0048				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 6 \text{ V}$	0.006				
I <sub>D</sub> (A)	16				
Configuration	Single				

#### **FEATURES**

- Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$\Gamma_{\rm C}$ = 25 °C, unles	ss otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	60	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	16	
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	9	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	6	Α	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	67		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50	
Single Pulse Avalanche Energy	L = 0.1 Min	E <sub>AS</sub>	125	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	7.1	W
	T <sub>C</sub> = 125 °C		2.3	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>b</sup>	$R_{thJA}$	80	°C/W		
Junction-to-Foot (Drain)		$R_{thJF}$	21	C/VV		

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				ı			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A	-	0.0048	-	Ω
Drain Caures On State Resistance		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C		0.011	-	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	0.015	-	
		V <sub>GS</sub> = 6 V	I <sub>D</sub> = 5 A	-	0.006	-	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6 A		-	25	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	2531	3165	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$ $V_{DS} = 25 V, f = 1 MHz$	-	382	480	рF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	153	195	1
Total Gate Charge <sup>c</sup>	Qg			-	45	68	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 12 \text{ A}$	-	9.9	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	11.2	-	
Gate Resistance	$R_g$	f = 1 MHz		0.40	0.87	1.30	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	20	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_L = 2.5 \Omega$ $I_D \cong 12 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	12	18	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	25	38	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	67	Α
Forward Voltage	V <sub>SD</sub>	$I_F = 1.7 \text{ A}, V_{GS} = 0$		-	0.72	1.2	V

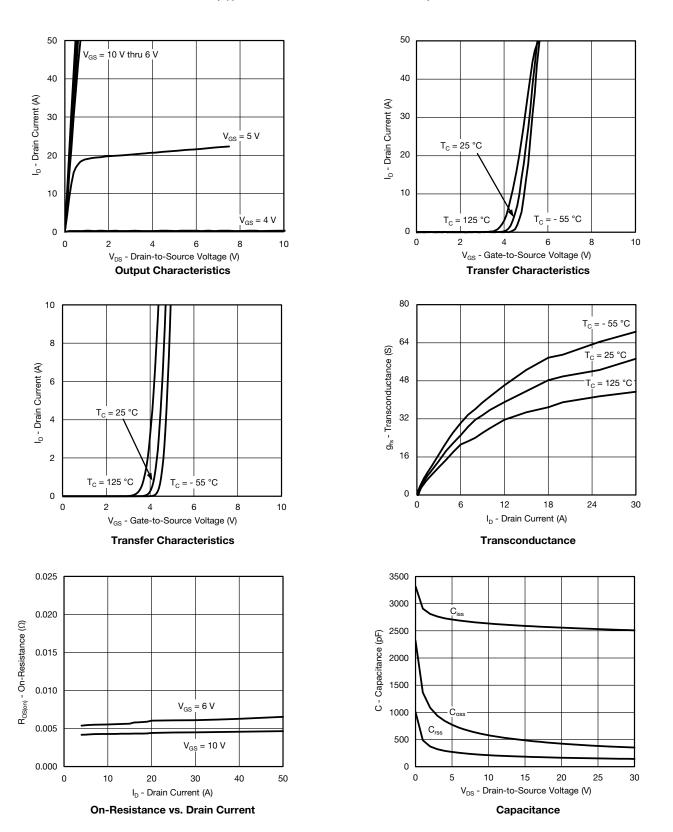
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

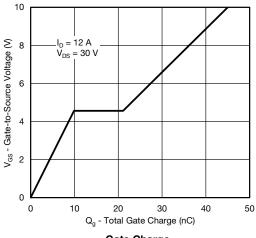


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

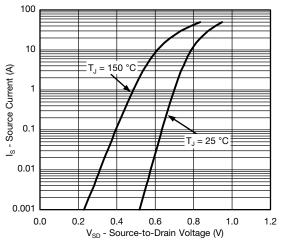




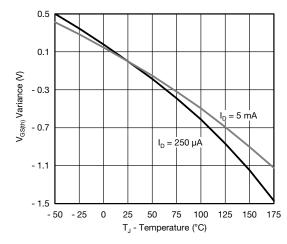
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



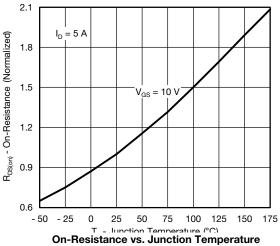


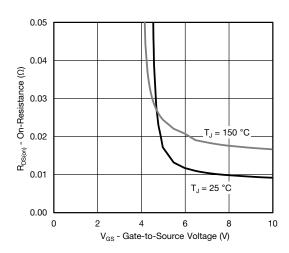


**Source Drain Diode Forward Voltage** 

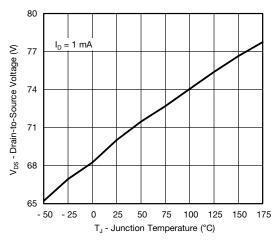


**Threshold Voltage** 





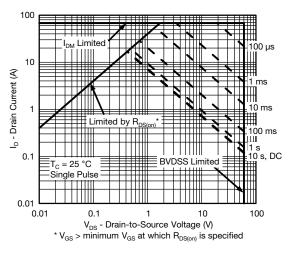
On-Resistance vs. Gate-to-Source Voltage



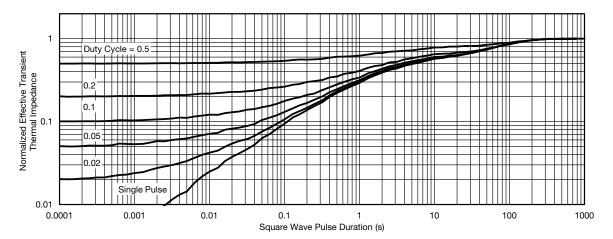
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

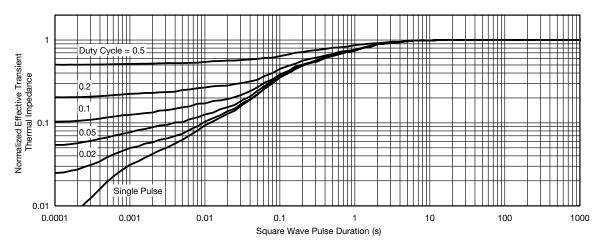


Normalized Thermal Transient Impedance, Junction-to-Ambient

服务热线:400-655-8788 5



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

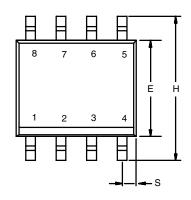
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

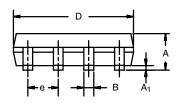
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

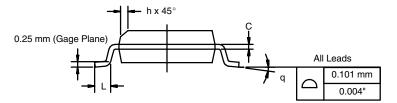
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**SOIC (NARROW): 8-LEAD**JEDEC Part Number: MS-012





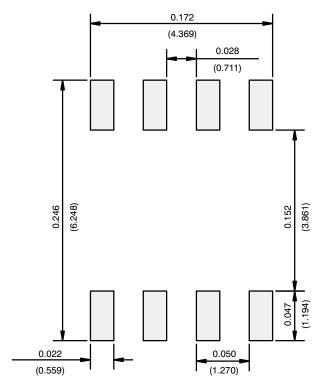


	MILLIN	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-0652	ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498



### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)



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